

Sirenza Microdevices' SGA-9089Z is a high performance Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) designed for operation from DC to 4.0 GHz. The SGA-9089Z is optimized for 3.0V operation. The device provides excellent linearity at a low cost. It can be operated over a wide range of currents depending on the power and linearity requirements.

The matte tin finish on Sirenza's lead-free "Z" package is applied using a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. The package body is manufactured with green molding compounds that contain no antimony trioxide or halogenated fire retardants.



# SGA-9089Z

# High IP3, Medium Power Discrete **SiGe Transistor**





## **Product Features**

- **DC-4 GHz Operation**
- Lead Free, RoHS Compliant & Green Package
- 15.0 dB Gmax @ 2.44 GHz
- P<sub>1dB</sub> = +23.8 dBm @ 2.44 GHz
- OIP<sub>3</sub> = +37.5 dBm @ 2.44 GHz
- 3.1 dB NF @ 2.44 GHz
- Low Cost, High Performance, Versatility

## Applications

- **Analog and Digital Wireless Systems**
- 3G, Cellular, PCS, RFID
- **Fixed Wireless, Pager Systems**
- PA stage for Medium Power Applications

Symbol	Parameters	Units	Frequency	Min.	Тур.	Max.	
G <sub>MAX</sub>	Maximum Available Gain	dB	880 MHz		23.2		
			1960 MHz		16.4		
			2440 MHz		15.0		
G	Power Gain	dB	880 MHz <sup>[1]</sup>		18.0		
	$7_{0}=7_{0}$		1960 MHz <sup>[2]</sup>		13.0		
	-SSOPI, -LLOPI		2440 MHz <sup>[2]</sup>		11.0		
P <sub>1dB</sub>	Output Dower at 1dD Compression <sup>[2]</sup>	dBm	880 MHz		23.7		
	7 - 7 - 7 - 7 - 7		1960 MHz		23.7		
	∠s−∠sopt, ∠l−∠lopt		2440 MHz		23.8		
OIP <sub>3</sub>	Output Third Orden Intersent Daint [2]	dBm	880 MHz		37.4		
			1960 MHz		37.5		
	∠s−∠sopt, ∠l−∠lopt		2440 MHz		37.5		
NF	Noise Figure <sup>[2]</sup>	dB	880 MHz		3.2		
			1960 MHz		3.1		
	∠s−∠sopt, ∠l−∠lopt		2440 MHz	880 MHZ 23.2   1960 MHz 16.4   2440 MHz 15.0   380 MHz <sup>[1]</sup> 18.0   960 MHz <sup>[2]</sup> 13.0   940 MHz <sup>[2]</sup> 13.0   440 MHz <sup>[2]</sup> 11.0   880 MHz 23.7   1960 MHz 23.7   2440 MHz 23.7   2440 MHz 23.8   880 MHz 37.4   1960 MHz 37.5   2440 MHz 37.5   880 MHz 37.5   880 MHz 37.5   880 MHz 37.5   2440 MHz 37.5   880 MHz 3.1   1960 MHz 3.1   2440 MHz 3.1   2440 MHz 3.1   100 180   5.7 6   48 1   93 Tone Spacing = 1MHz, Pout per tone = 10 dBm   Application Circuit 100			
h <sub>FE</sub>	DC Current Gain			100	180	300	
BV <sub>CEO</sub>	Collector - Emitter Breakdown Voltage	V		5.7	6		
Rth, j-l	Thermal Resistance (Junction - lead)	°C/W			48		
V <sub>CE</sub>	Device Operating Voltage (collector- emitter)	V				3.8	
I <sub>CE</sub>	Device Operating Current (collector - emitter)	mA				220	
<b>Test Conditions:</b> $V_{CE} = 3.0V$ , $I_{CE} = 170$ mA Typ. (unless noted otherwise), $T_L = 25^{\circ}$ C OIP <sub>3</sub> Tone Spacing = 1MHz, Pout per tone = 10 dBm							
[1] 100% production tested with Application Circuit [2] Data with Application Circuit							

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### Absolute Maximum Ratings

Parameter	Absolute Limit
Max Device Current (I <sub>CE</sub> )	235 mA
Max Base Current (I <sub>B</sub> )	2.5 mA
Max Device Voltage (V <sub>CE</sub> )	4.5 V
Max Collector - Base Voltage ( $V_{CB}$ )	12 V
Max Emitter - Base Voltage (V <sub>EB</sub> )	4.5 V
Max. RF Input Power* (See Note)	+24 dBm
Max. Junction Temp. (T <sub>J</sub> )	+150°C
Operating Temp. Range (T <sub>L</sub> )	See Graph
Max. Storage Temp.	+150°C

Load condition,  $Z_L = 50$  Ohms

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:  $I_D V_D < (T_J - T_L) / R_{TH}, j-I$  $T_L = T_{LEAD}$ 

Reliability & Qualification Information						
Parameter	Rating					
ESD Rating - Human Body Model (HBM)	Class 1C					
Moisture Sensitivity Level	MSL 1					
This product qualification report can be downloaded at						
www.sirenza.com						



# Maximum Recommended Operational

### **Caution: ESD sensitive**

Appropriate precautions in handling, packaging and testing devices must be observed.

# **Typical performance - Engineering Application Circuits**

Freq (MHz)	V <sub>CE</sub> (V)	I <sub>CE</sub> (mA)	P <sub>1dB</sub> (dBm)	OIP <sub>3</sub> (dBm)	Gain (dB)	S11 (dB)	S22 (dB)	NF (dB)	Ζ <sub>SOPT</sub> (Ω)	Ζ <sub>LOPT</sub> (Ω)
880	3	170	23.7	37.4	18.0	-18.6	-18.7	3.2	14.8 - j5.6	16.7 - j0.105
2440	3	170	23.8	37.5	11.0	-18.7	-23.9	3.1	11.1 - j23.5	16.4 - j14.2
Test Conditi	ons: $V_S = 5$	5V I	s = 180 mA Typ	D.	OIP <sub>3</sub> Tone	Spacing = 1	/Hz, Pout per	tone = 10 dBr	n TL = 25°C	

Data above represents typical performance of the application circuits. Refer to the application note for additional RF data, PCB layouts, and BOMs for each application circuit. The application note also includes biasing instructions and other key issues to be considered. For the latest application notes please visit our site at www.sirenza.com or call your local sales representative.



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http://www.sirenza.com EDS-105051 Rev B

SGA-9089Z Medium Power SiGe Discrete Transistor





### **Typical Performance - De-embedded S-parameters**

Note: S-parameters are de-embedded to the device leads with  $Z_s = Z_L = 50\Omega$ . The device was mounted on Sirenza's recommended evaluation board. De-embedded S-parameters can be downloaded from our website (www.sirenza.com)





#### Preliminary SGA-9089Z Medium Power SiGe Discrete Transistor



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